

2N2218, A, AL & 2N2219, A, AL



NPN Switching Silicon Transistor

Rev. V2

Features

- Available in JAN, JANTX, JANTXV and JANS per MIL-PRF-19500/251
- TO-5 & TO-39 (TO-205AD) Package



Electrical Characteristics

Parameter	Test Conditions	Part #	Units	Min.	Max.
Off Characteristics:					
Collector - Emitter Breakdown Voltage	$I_E = 10 \text{ mA}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL	Vdc	30 50	—
Emitter - Base Cutoff Current	$V_{EB} = 5 \text{ V}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL All types	μAdc nAdc	—	10
	$V_{EB} = 6 \text{ V}$				10
	$V_{EB} = 4 \text{ V}$				10
Collector - Emitter Cutoff Current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 50 \text{ V}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL	nAdc	—	10
Collector - Base Cutoff Current	$V_{CB} = 50 \text{ V}$ $V_{CB} = 60 \text{ V}$ $V_{CB} = 60 \text{ V}$ $V_{CB} = 75 \text{ V}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL	nAdc nAdc μAdc μAdc	—	10
					10
					10
					10
On Characteristics ¹ :					
Forward Current Transfer Ratio	$I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$	2N2218	—	20	—
		2N2219		35	—
		2N2218A/AL		30	—
		2N2219A/AL		50	—
	$I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$	2N2218		25	150
		2N2219		50	325
$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	2N2218A/AL	35	150		
	2N2219A/AL	75	325		
	2N2218	35	—		
	2N2219	75	—		
$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$	2N2218A/AL	40	—		
	2N2219A/AL	100	—		
$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$	2N2218A/AL	40	120		
	2N2219A/AL	100	300		
Collector - Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL	Vdc	—	0.4 0.3
	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL			1.6 1.0

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

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Electrical Specifications @ $T_A = 25^\circ\text{C}$

Parameter	Test Conditions	Part #	Units	Min.	Max.
On Characteristics ¹ :					
Base - Emitter Saturation Voltage	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL	Vdc	0.6 0.6	1.3 1.2
	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$	2N2218; 2N2219 2N2218A/AL; 2N2219A/AL		— —	2.6 2.0
Dynamic Characteristics:					
Small-Signal Short-Circuit, Forward Current Transfer Ratio	$I_C = 1\text{ mA}, V_{CE} = 20\text{ V}, 1\text{ kHz}$	2N2218 2N2219 2N2218A, AL 2N2219A, AL		25 50 35 75	—
Magnitude of Small-Signal Short-Circuit, Forward Current Transfer Ratio	$I_C = 20\text{ mA}, V_{CE} = 20\text{ V}, 100\text{ MHz}$	—		2.5	12
Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1\text{ MHz}$	—	pF	—	8
Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, 100\text{ kHz} \leq f \leq 1\text{ MHz}$	—	pF	—	25
Switching Characteristics ² :					
Turn-On Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$	2N2218, 2N2219 2N2218A, AL, 2N2219A, AL	ns	—	40 35
Turn-Off Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$	2N2218, 2N2219 2N2218A, AL, 2N2219A, AL	ns	—	250 300

2. For Turn-On time see figure 3, and for Turn-Off time see figure 4 of MIL-PRF-19500/251.

Absolute Maximum Ratings @ $T_C = 25^\circ\text{C}$

Parameter	2N2218 & 2N2219	2N2218A; AL & 2N2219A; AL
Collector - Emitter Voltage	30 Vdc	50 Vdc
Collector - Base Voltage	60 Vdc	75 Vdc
Emitter - Base Voltage	5 Vdc	6 Vdc
Collector Current	800 mA	
Total Power Dissipation ^{3,4} $T_A = +25^\circ\text{C}$ $T_C = +25^\circ\text{C}$	0.8 W 3.0 W	
Thermal Resistance, Junction to Case	50°C/W	
Operating & Storage Temperature	-55°C to +200°C	

3. Derate linearly 4.6 mW/°C above $T_A > +25^\circ\text{C}$.

4. Derate linearly 17.0 mW/°C above $T_C > +25^\circ\text{C}$.

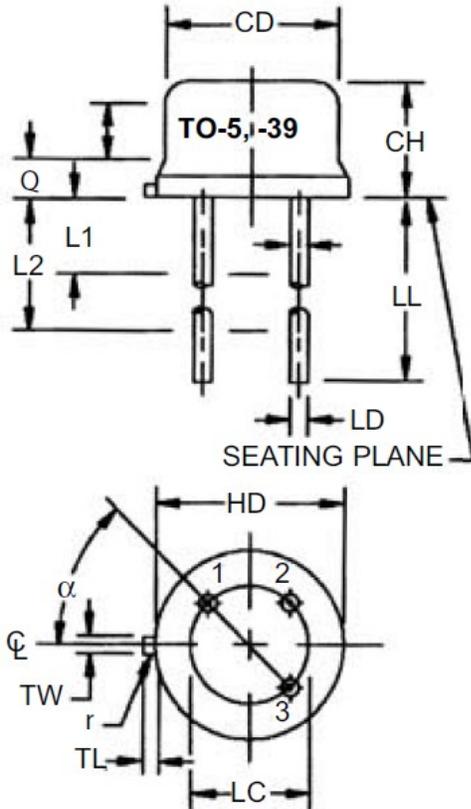
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Outline Drawing (TO-5 & TO-39)



LTR	Dimensions				Note
	Inches		Millimeters		
	Min.	Max.	Min.	Max.	
CD	0.305	0.335	7.75	8.51	—
CH	0.240	0.260	6.10	6.60	—
HD	0.335	0.370	8.51	9.40	—
LC	0.200 TP		5.08 TP		7
LD	0.016	0.019	0.41	0.48	8, 9
LL	See note 14				
LU	0.016	0.019	0.41	0.48	8, 9
L1	—	0.050		1.27	8, 9
L2	0.250	—	6.35	—	8, 9
P	0.100	—	2.54	—	7
Q	—	0.030	—	0.76	5
TL	0.029	0.045	0.74	1.14	3, 4
TW	0.028	0.034	0.71	0.86	3
r	—	0.010	—	0.25	10
α	45° TP		45° TP		7

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. CD shall not vary more than 0.010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
7. Leads at gauge plane 0.054 +0.001 -0.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within 0.007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
8. Dimension LU applies between L, and L,. Dimension LD applies between L, and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
9. All three leads.
10. The collector shall be internally connected to the case.
11. Dimension r (radius) applies to both inside corners of tab.
12. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.
13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
14. For non-S-suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For S-suffix types (TO-39), dimension LL = 0.5 inch (12.70 mm) min. and 750 inch (19.05 mm) max.

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